

LINEAR SYSTEMS

Over Three Decades of Quality Through Innovation

SD-SST211/213/215

N-CHANNEL LATERAL
DMOS SWITCH
ZENER PROTECTED

PRODUCT SUMMARY

PART NUMBER	$V_{(BR)DS}$ Min (V)	$V_{(GS)th}$ Max (V)	$r_{DS(on)}$ Max (Ω)	C_{rss} Max (pF)	t_{ON} Max (ns)
SD211DE	30	1.5	45 @ $V_{GS}=10V$	0.5	2
SD213DE	10	1.5	45 @ $V_{GS}=10V$	0.5	2
SD215DE	20	1.5	45 @ $V_{GS}=10V$	0.5	2
SST211	30	1.5	50 @ $V_{GS}=10V$	0.5	2
SST213	10	1.5	50 @ $V_{GS}=10V$	0.5	2
SST215	20	1.5	50 @ $V_{GS}=10V$	0.5	2

Features

- Ultra-High Speed Switching— t_{ON} : 1ns
- Ultra-Low Reverse Capacitance: 0.2pF
- Low Guaranteed r_{DS} @5V
- Low Turn-On Threshold Voltage
- N-Channel Enhancement Mode

Benefits

- High-Speed System Performance
- Low Insertion Loss at High Frequencies
- Low Transfer Signal Loss
- Simple Driver Requirement
- Single Supply Operation

Applications

- Fast Analog Switch
- Fast Sample-and-Holds
- Pixel-Rate Switching
- DAC Deglitchers
- High-Speed Driver

Description

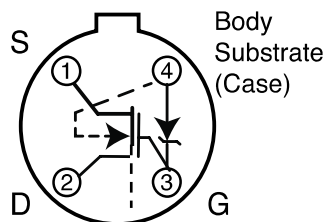
The SD211DE/SST211 series consists of enhancement-mode MOSFETs designed for high speed low-glitch switching in audio, video and high-frequency applications. The SD211 may be used for a ± 5 -V analog switching or as a high speed driver of the SD214. The SD214 is normally used for ± 10 -V analog switching. These MOSFETs utilize lateral construction to achieve low

capacitance and ultra-fast switching speeds. An integrated ZENER diode provides ESD protection. These devices feature a poly-silicon gate for manufacturing reliability.

For similar products see: quad array—SD5000/5400 series, non-Zener protection—SD210DE/214DE.

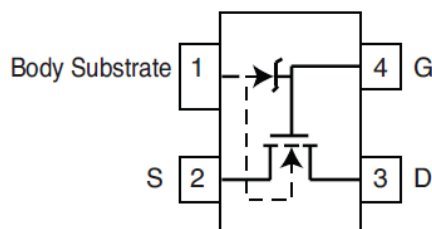
TOP VIEW

SD211DE, SD213DE, SD215DE



TO-206AF
(TO-72)

TO-253 (SOT-143)



TOP VIEW
SST211, SST213, SST215

Absolute Maximum Ratings (T_A = 25°C unless otherwise noted)

Gate Drain, Gate Source Voltage	(SD211DE/SST211) -30/25V (SD213DE/SST213) -15/25V (SD215DE/SST215) -25/30V	Drain-Substrate Voltage	(SD211DE/SST211) 30V (SD213DE/SST213) 15V (SD215DE/SST215) 25V
Gate-Substrate Voltage ^a	(SD211DE/SST211) -0.3/25V (SD213DE/SST213) -0.3/25V (SD215DE/SST215) -0.3/30V	Source-Substrate Voltage	(SD211DE/SST211) 15V (SD213DE/SST213) 15V (SD215DE/SST215) 25V
Drain-Source Voltage	(SD211DE/SST211) 30V (SD213DE/SST213) 10V (SD215DE/SST215) 20V	Drain Current 50mA
Voltage	(SD211DE/SST211) 10V (SD213DE/SST213) 10V (SD215DE/SST215) 20V	Lead Temperature (1/16" from case for 10 seconds) 300°C
		Storage Temperature -65 to 150°C
		Operating Junction Temperature -55 to 125°C
		Power Dissipation 300mW

Notes:
a. Derate 3mW/°C above 25°C

Specifications^a

PARAMETER	SYMBOL ^b	TEST CONDITIONS ^b	TYP ^b	LIMITS						UNIT	
				211 Series		213 Series		215 Series			
				Min	Max	Min	Max	Min	Max		
Static											
Drain - Source Breakdown Voltage	V _{(BR)DS}	V _{GS} = V _{BS} = 0V, I _D = 10 μA	35	30						V	
		V _{GS} = V _{BS} = -5V, I _D = 10 nA	30	10		10		20			
Source - Drain Breakdown Voltage	V _{(BR)SD}	V _{GS} = V _{BD} = -5V, I _S = 10 nA	22	10		10		20			
Drain - Substrate Breakdown Voltage	V _{(BR)DBO}	V _{GB} = 0V, I _D = 10 nA Source Open	35	15		15		25			
Source - Substrate Breakdown Voltage	V _{(BR)SBO}	V _{GB} = 0V, I _S = 10 μA Drain Open	35	15		15		25			
Drain - Source Leakage	I _{DS(off)}	V _{GS} = V _{BS} = -5V	V _{DS} = 10V	0.4		10		10		nA	
			V _{DS} = 20V	0.9					10		
Source - Drain Leakage	I _{SD(off)}	V _{GD} = V _{BD} = -5V	V _{SD} = 10V	0.5		10		10			
			V _{SD} = 20V						10		
Gate Leakage	I _{GBS}	V _{DB} = V _{SB} = 0V, V _{GB} = 30V	0.01		100		100		100		
Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 1 μA, V _{SB} = 0V	0.8	0.5	1.5	0.1	1.5	0.1	1.5	V	
Drain - Source On-Resistance	r _{DS(on)}	V _{SB} = 0V I _D = 1mA	V _{GS} = 5V (SD Series)	58		70		70		70	Ω
			V _{GS} = 5V (SST Series)	60		75		75		75	
			V _{GS} = 10V (SD Series)	38		45		45		45	
			V _{GS} = 10V (SST Series)	40		50		50		50	
			V _{GS} = 15V	30							
			V _{GS} = 20V	26							
			V _{GS} = 25V	24							

Specifications^a

PARAMETER	SYMBOL ^b	TEST CONDITIONS ^b	TYP ^c	LIMITS						UNIT	
				211 Series		213 Series		215 Series			
				Min	Max	Min	Max				
Dynamic											
Forward Transconductance	g_{fs}	$V_{DS} = 10V, V_{SB} = 0V, I_D = 20mA, f = 1kHz$	SD Series	11	10		10		10		mS
	g_{os}		SST Series	10.5	9		9		9		
			All	0.9							
Gate Node Capacitance	$C_{(GS+GD+GB)}$	$V_{DS} = 10V, f = 1MHz, V_{GS} = V_{BS} = -15V$	SD Series	2.5			3.5		3.5		pF
Drain Node Capacitance	$C_{(GD+DB)}$				1.1			1.5		1.5	
Source Node Capacitance	$C_{(GS+SB)}$		SST Series	3.7			5.5		5.5		
Reverse Transfer Capacitance	C_{rss}		SST Series	4.2							
			SD Series	0.2			0.5		0.5		
Switching											
Turn-On Time	$t_{D(on)}$	SD Series Only $V_{SB} = 0V, V_{IN} 0 \text{ to } 5V, R_G = 25\Omega, V_{DD} = 5V, R_L = 680\Omega$		0.5			1		1		ns
	t_r			0.6			1		1		
Turn-Off Time	$t_{D(off)}$			2							
	t_f			6							

Notes:

- $T_A = 25^\circ C$ unless otherwise notes.
- B is the body (substrate) and $V_{(BR)}$ is breakdown voltage.
- Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.

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